M.Sc. DEGREE EXAMINATION, NOVEMBER - 2023

First Semester

Nanoscience and Technology

INTRODUCTION TO QUANTUM PHYSICS

(CBCS – 2022 onwards)

Time : 3 Hours

Maximum : 75 Marks

Part A $(10 \times 1 = 10)$

Answer **all** the following objective questions by choosing the correct option.

- 1. Which of the following statement is incorrect? (CO1, K2)
 - (a) If two operators have a common set of Eigen vectors then they commute
 - (b) Two non-degenerate commuting operators have a common set of Eigen vectors
 - (c) Eigen values of a Hermitian operator belonging to different eigen functions are real
 - (d) All eigen values of Hermitian operators are real and the eigen vectors belonging to the same eigen values are orthogonal
- 2. In terms of bra and ket vectors, the definition of the inner product of the state vectors Ψ_a and Ψ_b takes the form $(\Psi_a, \Psi_b) =$ (CO1, K2)
 - (a) < a b > (b) < b a >
 - (c) $\langle a a b \rangle$ (d) $\langle a b a b \rangle$

3.	Pau	li's exclusion princ	iple st	ates that	(CO2, K2)	
	(a)	two electrons ca same				
	(b)	no two electrons same	can h	ave all the quantu	ım numbers	
	(c)	particles with in exist in the same	teger state	and half integer	spin cannot	
	(d)	none of the above)			
4.	In repi	wave mechanics a resented by a	an in	cident beam of —— wave in incide	particles is ent channel. (CO2, K2)	
	(a)	circular	(b)	spherical		
	(c)	plane	(d)	stationary		
5.	Tur	nelling effect resul	ts in		(CO3, K3)	
	(a)	the escape of neu	trons			
	(b)	the production of	gamr	na rays		
	(c)	the leakage of alg	oha pa	articles		
	(d)	none of these				
6.	The	scattered particles	will		(CO3, K3)	
	(a)	Converges	(b)	Diverges		
	(c)	Split	(d)	Disperse		
7.	In l cont	now many dimensi fined?	ons, t	he quantum dot o	excitons are (CO4, K5)	
	(a)	0 D	(b)	1 D		
	(c)	2 D	(d)	3 D		
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		Par	rt B		$(5 \times 5 = 25)$
	(c)	both	(d)	none of the above	е
	(a)	heat	(b)	light	
10.	In ส betw	an indirect bandg reen conduction ba	gap s ind a	semiconductor, a nd valance band	transition l results in (CO5, K3)
	(c)	Valence band	(d)	Does not exist	
	(a)	Free band	(b)	Conduction band	l
9.	Free	electrons exist in			(CO5, K3)
	(d)	Acceptor fluoropho	ore is	at relatively high	frequency
	(c)	Low energy fluoro	phore	e is quenched	
	(b)	The transfer occu dipole coupling	rs th	rough intermolec	ular dipole-
	(a)	The energy transfe	er is 1	radiative	
8.	Whie	ch of the following i	s wro	ong about FRET?	(CO4, K5)

Answer **all** the questions not more than 500 words each.

11. (a) Define Eigen values and Eigen functions. (CO1, K2)

Or

(b) Covert matrix A to its inverse. (CO1, K2) $A = \begin{bmatrix} 2 & 4 & 6 \\ 4 & 2 & 3 \\ 3 & -3 & 1 \end{bmatrix}$

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12. (a) Express and explain Planck's quantum hypothesis. (CO2, K2)

Or

(b)	Show	the	failure	of	classical	mec	hanics	in
	explain	ning E	linstein's	phot	toelectric e	ffect.	(CO2,	K2)

13. (a) Identify the non-allowed state for a free particle in a box. (CO3, K3)

Or

- (b) Why a particle trapped in a box cannot be at rest? (CO3, K3)
- 14. (a) Measure the size effect in high dielectric constants materials. (CO4, K5)

Or

- (b) What is size effect? Assess the size-dependency of optical properties. (CO4, K5)
- 15. (a) Explain the construction of a p-n junction in a semiconductor. (CO5, K3)

Or

 (b) Prove that the Fermi level is lies exactly in between conduction band and valance band of intrinsic semiconductor. (CO5, K3)

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Part C $(5 \times 8 = 40)$

Answer **all** the questions not more than 1000 words each.

16. (a) Explain and relate beta and gamma functions. (CO1, K2)

Or

- (b) Classify and compare Legendre's polynomial and Hermite's polynomial and give their condition for orthogonality. (CO1, K2)
- 17. (a) Derive the expression for time independent Schrodinger wave equation. (CO2, K2)

Or

- (b) Explain the Uncertainty principle and show that the Uncertainty principle is a natural consequence of wave particle duality. (CO2, K2)
- 18. (a) Calculate the energy Eigen values and Eigen functions for the motion of a particle in a 2D well. (CO3, K3)

Or

- (b) Solve Schrodinger equation for a particle confined to an infinite potential box of width L in order to derive the expression for energy eigen values. (CO3, K3)
- 19. (a) Explain the size effect in π -conjugated and strongly interacting π -conjugated systems. (CO4, K5)

\mathbf{Or}

(b) Interpret the size effect in electromagnetic interactions between molecules and explain FRET. (CO4, K5)

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20. (a) Explain the origin of energy bands and solids and illustrate an E-k diagram. (CO5, K3)

Or

(b) Explain the process of band gap modification in a semiconductor optoelectronic material. (CO5, K3)

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M.Sc. DEGREE EXAMINATION, NOVEMBER 2023.

First Semester

Nanoscience and Technology

BASICS OF MATERIALS SCIENCE

(CBCS – 2022 onwards)

Time : 3 Hours

Maximum : 75 Marks

Part A $(10 \times 1 = 10)$

Answer **all** the following objective questions by choosing the correct option.

1.	The number	of lattice	points	in	the	rhombohedral	unit
	cell is					(CO1	, K1)

(a)	8		(b)	4

(c) 2 (d) 1

2. The tetragon has

(CO1, K1)

- (a) 4 faces (b) 12 edges
- (c) 6 corners (d) 8 edges
- 3. Primary bonds have energy range in kJ mol⁻¹ (CO2, K2)

(a)	1000 - 5000	(b)	10 - 100
(c)	100 - 1000	(d)	1 - 10

4.	The transition fr paramagnetic state is	om t. s name	l after	c to the (CO2, K2)
	(a) Curie	(b)	Curie - Weiss	
	(c) Neel	(d)	Debye	
5.	Pure silicon at 0 K is	an		(CO3, K4)
	(a) Intrinsic semico	onducto	r	
	(b) Extrinsic semic	onducto	or	
	(c) Metal (d) Insulator			
6	The unit of relative d	ioloctri	e constant is	(CO3 K4)
0.	(a) Dimonsionloss	(h)	E constant is $E m^{-1}$	(005, 114)
	(a) $C V^{-1}$	(d)	F m $F C^{-1}$	
	$(\mathbf{C}) \mathbf{C} \mathbf{V}$	(u)	I' C	
7.	The bulkiest side gro	up in tł	ne monomer is in	(CO4, K2)
	(a) Teflon	(b)	PVC	
	(c) PTFE	(d)	Polystyrene	
8.	The factors that pro	omote	non-crystallinity i	n polymers
	are			(CO4, K2)
	are (a) Large random s	ide gro	ups	(CO4, K2)
	are (a) Large random s (b) Branching	ide gro	ups	(CO4, K2)
	 are (a) Large random s (b) Branching (c) Addition of plase 	ide gro ticizers	ups	(CO4, K2)
	 are (a) Large random s (b) Branching (c) Addition of plass (d) All the above 	ide gro ticizers	ups	(CO4, K2)
9.	are (a) Large random s (b) Branching (c) Addition of plas (d) All the above A cation vacancy and type AB is called	ide gro ticizers l an ani	ups on vacancy in a cr	(CO4, K2) rystal of the (CO5, K2)
9.	 are (a) Large random s (b) Branching (c) Addition of plass (d) All the above A cation vacancy and type AB is called (a) Schottky defect 	ide gro ticizers l an ani (b)	ups on vacancy in a cr Frenkel defect	(CO4, K2) rystal of the (CO5, K2)
9.	 are (a) Large random s (b) Branching (c) Addition of plass (d) All the above A cation vacancy and type AB is called (a) Schottky defect (c) Pair of vacancie 	ide gro ticizers l an ani (b) es (d)	ups on vacancy in a cr Frenkel defect None of the abov	(CO4, K2) rystal of the (CO5, K2) e
9. 10.	 are (a) Large random s (b) Branching (c) Addition of plass (d) All the above A cation vacancy and type AB is called (a) Schottky defect (c) Pair of vacancie The t vector is paral the type: 	ide gro ticizers l an ani (b) es (d) lel to tl	ups on vacancy in a cr Frenkel defect None of the abov ne b vector in a di	(CO4, K2) rystal of the (CO5, K2) e slocation of (CO5, K2)
9. 10.	 are (a) Large random s (b) Branching (c) Addition of plass (d) All the above A cation vacancy and type AB is called (a) Schottky defect (c) Pair of vacancies The t vector is paral the type: (a) Edge 	ide gro ticizers l an ani (b) es (d) lel to tl	ups on vacancy in a cr Frenkel defect None of the abov ne b vector in a di Minod	(CO4, K2) rystal of the (CO5, K2) e slocation of (CO5, K2)
9. 10.	 are (a) Large random s (b) Branching (c) Addition of plass (d) All the above A cation vacancy and type AB is called (a) Schottky defect (c) Pair of vacancies The t vector is paral the type: (a) Edge 	ide gro ticizers l an ani (b) es (d) lel to tl (b)	ups on vacancy in a cr Frenkel defect None of the abov ne b vector in a di Mixed	(CO4, K2) rystal of the (CO5, K2) e slocation of (CO5, K2)

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Part B $(5 \times 5 = 25)$

Answer all the questions not more than 500 words each.

11. (a) Determine the packing fraction efficiency of a face-centered cubic system. (CO1, K1)

 \mathbf{Or}

- (b) Write a short note on Schottky and Frenkel defects. (CO1, K1)
- 12. (a) List out the differences between crystalline and amorphous solids. (CO2, K2)

 \mathbf{Or}

(b) Explain the optical properties of the solids.

(CO2, K2)

13. (a) What is an n-type and p-type semiconductors? (CO3, K4)

Or

- (b) Write a short note on p-n junction diodes. (CO3, K4)
- 14. (a) Explain the crystallinity of long-chain polymers. (CO4, K2)

Or

- (b) What is meant by the Flexural property of the polymer? (CO4, K2)
- 15. (a) Write a short note on twin boundaries. (CO5, K2)

Or

(b) Explain how defects influence the properties of solids. (CO5, K2)

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Part C $(5 \times 8 = 40)$

Answer **all** the questions not more than 1000 words each.

16. (a) Explain the principle and working of X-ray diffractometer with a suitable example. (CO1, K1)

 \mathbf{Or}

(b)	Discuss the	types of crystal	systems. ((CO1, K1	L)
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17. (a) Give a detailed description of the structure of silica and silicates. (CO2, K2)

Or

- (b) Explain the electrical and magnetic properties of solids with suitable examples. (CO2, K2)
- 18. (a) Deduce the expression for the carrier concentration in the intrinsic semiconductor. (CO3, K4)

Or

- (b) With a neat diagram, explain the working of junction transistors and junction lasers. (CO3, K4)
- 19. (a) Explain the classification of polymers with examples. (CO4, K2)

Or

- (b) Elaborate how macroscopic deformation occurs in semi-crystalline polymers. (CO4, K2)
- 20. (a) Briefly explain the surface and volume defects. (CO5, K2)

Or

(b) Explain Hall-Petch behaviour and the deformation in FEE nanostructures. (CO5, K2)

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Sub. Code	
533103	

M.Sc. DEGREE EXAMINATION, NOVEMBER - 2023

First Semester

Nanoscience and Technology

BASIC BIOTECHNOLOGY

(CBCS - 2022 onwards)

Time : 3 Hours

Maximum : 75 Marks

 $(10 \times 1 = 10)$

Answer **all** following objective questions by choosing the correct option.

Part A

1. Molecules in which the atoms are held together by ______ bonds have the strongest chemical linkages.

(CO1, K1)

- (a) Covalent Bond (b) Ionic Bond
- (c) Hydrogen Bond (d) Vanderwaal force
- 2. Polysaccharides often called as animal starch is (CO1, K1)
 - (a) Starch (b) Glycogen
 - (c) Inulin (d) Dextrin
- 3. A gene produced for rDNA technology contains a gene from one organism joined to the regulatory sequence of another gene. Such gene is called as (CO2, K2)
 - (a) Oncogene (b) Chimeric gene
 - (c) Junk gene (d) Mutant gene
- 4. Which of the following group of enzymes are popularly called as "Molecular stichers"? (CO2, K2)
 - (a) Restriction endonucleases
 - (b) Ligases
 - (c) RNA polymerases
 - (d) DNA polymerases

- The formation of embryoids from the pollen grains in the tissue culture medium is due to ______ (CO3, K3)
 (a) Organogenesis (b) Cellular totipotency
 (c) Test tube culture (d) Double fertilization
 The production of secondary metabolites requires the use of (CO3, K3)
 - (a) Meristem (b) Protoplast
 - (c) Axillary buds (d) Cell suspension
- 7. First human protein produced through recombinant DNA technology is (CO4, K3)
 - (a) Insulin (b) Erythropoietin
 - (c) Interferon (d) Growth hormone
- 8. Type of cell culture prepared by directly inoculating from of the tissue of the organism in culture media is (CO4, K4)
 - (a) Primary cell culture
 - (b) Secondary cell culture
 - (c) Cell lines
 - (d) Transformed cell lines
- 9. Which one of the following is not a green house gas?

(CO5, K6)

- (a) Ammonia (b) Carbon monoxide
- (c) Nitrous oxide (d) Methane
- 10. Use of plants or their products to degrade the pollutant to less toxic/non toxic products are termed as (CO5, K6)
 - (a) Bioleaching
 - (b) Bioremediation
 - (c) Phytoremediation
 - (d) PhycoreMediation

 $\mathbf{2}$

Part B
$$(5 \times 5 = 25)$$

Answer all the questions not more than 500 words each.

11. (a) Explain the structure of eukaryotic cell with suitable illustrations. (CO1, K1)

Or

- (b) Enumerate the salient features of Watson-Crick model of DNA. (CO1, K1)
- 12. (a) Elaborate the method used for secondary screening of recombinants. (CO2, K2)

Or

- (b) Briefly explain the merits, ethical and social issues of gene cloning. (CO2, K2)
- 13. (a) Enlist the various components and parameters to be considered for the construction of green house.

(CO3, K3)

Or

- (b) Agrobacterium species is termed as nature's genetic engineer – Justify. (CO3, K3)
- 14. (a) Explain the characteristic features of primary and immortal cell lines. (CO4, K3)

 \mathbf{Or}

- (b) Briefly explain the various physical methods of gene transfer. (CO4, K3)
- 15. (a) Explain in detail the role of microbial biotechnology in clearing oil spills in marine environment.

(CO5, K6)

Or

(b) Outline the steps involved production of biogas.

(CO5, K6)

3

Part C

 $(5 \times 8 = 40)$

Answer all the questions not more than 1,000 words each.

16. (a) Explain in detail classification, structure of heteropolysaceharides and its biological significance. (CO1, K1)

 \mathbf{Or}

- (b) Derive the Michaelis-Menten equation for an enzyme catalyzed reaction. How MM equation can be linearized? (CO1, K1)
- 17. (a) Outline the steps involved in recombinant DNA technology and add a note on its applications.

(CO2, K2)

 \mathbf{Or}

- (b) Discuss in detail *in vivo* and *ex vivo* gene therapy with suitable examples. (CO2, K2)
- 18. (a) Elaborate the various stages of micropropagation and its advantages. Cite suitable examples for horticulture plants. (CO3, K3)

Or

- (b) Summarize your idea about "Biopharming" of plants for the production of recombinant proteins.(CO3, K3)
- 19. (a) Give a detailed account on typos of cell culture media and its composition. (CO4, K3)

Or

- (b) Enumerate the steps involved in construction of transgenic animals. Add a note on its biomedical applications. (CO4, K3)
- 20. (a) Elaborate in detail the sources and steps involved in single cell protein synthesis, its merits and demerits. (CO5, K6)

Or

(b) Discuss in detail about phytoremediation techniques for waste water treatment. (CO5, K6)

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M.Sc. DEGREE EXAMINATION, NOVEMBER - 2023

First Semester

NanoScience and Technology

INTRODUCTION TO NANOSCIENCE

(CBCS – 2022 onwards)

Time : 3 Hours

Maximum : 75 Marks

Part A $(10 \times 1 = 10)$

Answer **all** the following objective questions by choosing the correct option

- 1. Which one of the following explains the behaviour of matter at the atomic scale? (CO1, K2)
 - (a) Classical (b) Quantum
 - (c) Both (a) and (b) (d) None of the above
- 2. Which one of the following nanomaterials comes under two-dimensional? (CO1, K2)
 - (a) Nanoparticles (b) Nanorods
 - (c) Nanofilms (d) Bundles of nanowires
- 3. The melting point of particles in nano form (CO2, K3)
 - (a) Increases
 - (b) Decreases
 - (c) Increases then decreases
 - (d) Remains same

The	first talk about	nan	o-technology was	given by (CO2, K3)
(a)	Richard Feynman	(b)	Albert Einstein	
(c)	Newton	(d)	George D. Moore	
Whic appr	ch of the followi oach of the synthes	ng is sis of	s an example of nanomaterial?	f top-down (CO3, K6)
(a)	Physical vapour d	eposi	tion	
(b)	Sputtering			
(c)	Chemical vapour	depos	sition	
(d)	Mechanical attriti	on		
In a adjao	bucky ball, each ca cent carbon atoms.	rbon	atom is bound to –	(CO3, K6)
(a)	4	(b)	3	
(c)	2	(d)	1	
The	most important pro	operty	y of nanomaterials	is (CO4, K4)
(a)	Friction	(b)	Force	
(c)	Pressure	(d)	Temperature	
The	hardest material fo	undi	in nature is ——	
				(CO4, K4)
(a)	Steel	(b)	Topaz	
(c)	Diamond	(d)	Graphite	
Whic for d	ch property of nan- iffusion?	opart	icles provides a di	riving force (CO5, K3)
(a)	Optical properties	i i		
(b)	High surface-to-ve	olume	e ratio	
(c)	Sintering			
(d)	None of the above			

 $\mathbf{2}$

10.	Silica	a coated iron oxide nanoparticles are used in (CO5, K3)
	(a)	Structural and mechanical materials
	(b)	Electronics
	(c)	Magnetic applications
	(d)	Medical diagnosis
		Part B $(5 \times 5 = 25)$
1	Answe	r all the questions not more than 500 words each.
11.	(a)	Write a short note on ceramics. (CO1, K2)
		Or
	(b)	Explain the significance of nanoscale materials. (CO1, K2)
12.	(a)	What is the difference between nucleation and growth? (CO2, K3)
		Or
	(b)	Write a short note on 2D nanostructures. (CO2, K3)
13.	(a)	Explain the differences between the properties of bulk and microscopic materials. (CO3, K6)
		Or
	(b)	Give a short note on the optical properties of nanomaterials. (CO3, K6)
14.	(a)	What is meant by grain boundaries? (CO4, K4)
		Or
	(b)	Write a short note on intermolecular forces.

(CO4, K4)
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15.	(a)	Explain superhydrophobicity.	(CO5, K3)
		Or	
	(b)	Write a short note on biochips.	(CO5, K3)
		Part C	$(5 \times 8 = 40)$
A	nswer	all the questions not more than 1000 wor	rds each.
16.	(a)	Explain the different types of nanomater	ials. (CO1, K2)
		Or	
	(b)	Discuss the background of Nanotechnolog its fundamental scientific implications.	gy based on (CO1, K2)
17.	(a)	Explain how the properties of nanoma influenced by the size of nanomaterials.	terials are (CO2, K3)
		Or	
	(b)	With a neat diagram, explain the phenucleation and growth of nanomaterials.	enomena of (CO2, K3)
18.	(a)	Explain the electrical and mechanical pananomaterials.	roperties of (CO3, K6)
		Or	
	(b)	Give a detailed description of nanomaterials with examples.	biological (CO3, K6)
19.	(a)	Explain the different types of nanocrystal	ls.
			(CO4, K4)
		\mathbf{Or}	
	(b)	Elaborate the similarities and difference the intermolecular and interparticle force	es between es.
			(CO4, K4)
20.	(a)	applications.	(CO5, K3)
		Or	
	(b)	How nanomaterials are useful in the cosmetic applications.	e food and (CO5, K3)

4

M.Sc. DEGREE EXAMINATION, NOVEMBER - 2023

First Semester

Nanoscience and Technology

Elective : THIN FILM TECHNOLOGIES AND CHARACTERISTICS

(CBCS – 2022 onwards)

Time : 3 Hours

Maximum : 75 Marks

Part A $(10 \times 1 = 10)$

Answer **all** the following objective type questions by choosing the correct option.

- 1. Give the thickness range of the film used in thin film technology (CO1, K1)
 - (a) 0.5-2.5 mm
 - (b) 0.02-8 mm
 - (c) 10-20 mm
 - (d) 0.05-0.07 mm
- 2. How is the process of film deposition carried out in cathode sputtering? (CO1, K1)
 - (a) Slower than evaporation method
 - (b) Faster than evaporation method
 - (c) Similar to same as evaporation method
 - (d) All of the mentioned

3. What is nucleation in crystallization?

(CO2, K2)

- (a) It is the initial step in crystallization
- (b) It is the final step in crystallization
- (c) It is the step where nucleus is added
- (d) It is the sub category crystallization

4.	Whie nucle	ch of eation a	the are co	following statements prrect?		about primary (CO2, K2)						
	State	ement	1:	The call	e appear ed prima	rance ary nu	of the cleation	first n tim	cr e.	yst	al	is
	State	ement 2	2:	It pha	describe .se.	s the	trans	ition	to	a	ne	w
	(a)	True,	False	;	(b)	True	, True					
	(c)	False,	True	;	(d)	False	e, False)				

- 5. What is the primary purpose of chemical vapor deposition (CVD) in the manufacturing industry? (CO3, K2)
 - (a) To coat or deposit thin films on a substrate
 - (b) To create a vacuum within a chamber
 - (c) To remove material from a substrate
 - (d) To produce mechanical vibrations
- 6. In physical vapor deposition (PVD), which of the following processes is used to create a thin film on a substrate? (CO3, K2)
 - (a) Chemical reactions between liquid precursors
 - (b) Erosion of the substrate material
 - (c) Evaporation of solid source material
 - (d) Electrochemical plating

 $\mathbf{2}$

- 7. Which of the following epitaxial growth techniques typically involves the precise deposition of individual atoms or molecules in a high-vacuum environment? (CO4, K2)
 - (a) Chemical Vapor Deposition (CVD)
 - (b) Molecular Beam Epitaxy (MBE)
 - (c) Metalorganic Vapor Phase Epitaxy (MOVPE)
 - (d) Liquid Phase Epitaxy (LPE)
- 8. Which epitaxial growth technique often involves the use of liquid-phase solutions to deposit a crystalline layer on a substrate? (CO4, K2)
 - (a) Chemical Vapor Deposition (CVD)
 - (b) Metalorganic Vapor Phase Epitaxy (MOVPE)
 - (c) Molecular Beam Epitaxy (MBE)
 - (d) Liquid Phase Epitaxy (LPE)
- 9. Which of the following is a characteristic of thin films?

(CO5, K5)

- (a) Thickness typically ranges from millimeters to centimeters
- (b) They are opaque and do not transmit light
- (c) Surface roughness is not a concern in thin film applications
- (d) They can exhibit unique optical and electronic properties due to their size and structure
- 10. What is the key application of thin films in the field of electronics? (CO5, K5)
 - (a) Building large-scale infrastructure projects
 - (b) Producing bulk materials for construction
 - (c) Creating integrated circuits and thin-film transistors
 - (d) Manufacturing heavy machinery

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Part B $(5 \times 5 = 25)$

Answer **all** the questions not more than 500 words.

11.	(a)	Explain Hertz Knudsen equation.	(CO1, K1)
		Or	
	(b)	Explain how plasma properties can be during glow discharge for specific	controlled purposes. (CO1, K1)
12.	(a)	Explain the concept of nucleation in formation.	thin film (CO2, K2)
		Or	
	(b)	Describe the self-assembly process.	(CO2, K2)
13.	(a)	Describe adsorption and Surface	diffusion. (CO3, K2)
		Or	
	(b)	Explain Lattice mismatch and surface n in thin film deposition technology.	norphology (CO3, K2)
14.	(a)	What is meant by homo and hetero	o epitaxy? (CO4, K2)
		Or	
	(b)	Describe bandgap engineering in epitaxy technology.	v thin film (CO4, K2)
15.	(a)	Explain mechanical and electrical properties film.	ties of thin (CO5, K5)
		Or	
	(b)	Describe multilayer thin films.	(CO5, K5)
		4	R0268

Part C $(5 \times 8 = 40)$

Answer all the questions not more than 1,000 words each.

16. (a) Describe the key process involved in thin film deposition and provide examples of different deposition methods. (CO1, K1)

Or

- (b) Explain the concept of Sputtering as a thin film deposition technique. (CO1, K1)
- 17. (a) Explain the stages involved in nucleation, the mechanisms that govern the growth of thin film, and the factors that impact the thin film structure. (CO2, K2)

Or

- (b) Write about the mechanism and controls for nanostructure of 0 and 1 dimension. (CO2, K2)
- 18. (a) Describe any four factors that influence the process of nucleation and growth in deposition technology. (CO3, K2)

Or

- (b) Explain growth monitoring and composition control in thin film deposition technology of semiconductor devices. (CO3, K2)
- 19. (a) Summarize the epitaxy technology and its classification. (CO4, K2)

Or

(b) Explain Molecular bean epitaxy. (CO4, K2)

 $\mathbf{5}$

20. (a) Explain various thin film properties for industrial application. (CO5, K5)

Or

(b) Explain the monolayer and Multilayer films. How to analyze it? (CO5, K5)

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M.Sc. DEGREE EXAMINATION, NOVEMBER - 2023

Third Semester

Nanoscience And Technology

NANOBIOTECHNOLOGY AND NANOMEDICINE

(CBCS – 2022 onwards)

Time : 3 Hours

Maximum : 75 Marks

Part A $(10 \times 1 = 10)$

Answer **all** following objective questions by choosing the correct option.

- - (a) Dendrimers
 - (b) Metal based materials
 - (c) Carbon based materials
 - (d) Composites
- 2. Spherical gold nanoparticles are dimensional nanomaterials (CO1, K2)
 - (a) Zero (b) Two
 - (c) One (d) Three

3.		——— is used	as	vehicle to deliver desired		
	mol	ecules into the seed	s dar	g germination. (CO2, K6)		
	(a)	CNT	(b)	CNF		
	(c)	CNR	(d)	CNP		
4.	Gut	buster is a nano —		(CO2, K6)		
	(a)	herbicide	(b)	weedicide		
	(c)	nematicide	(d)	insecticide		
5.	Qua	ntum dots are ——		— in nature (CO3, K6)		
	(a)	inorganic	(b)	organic		
	(c)	metallic	(d)	biologic		
6.	In g	lucose electrode, gl	lucose	e oxidase has been coupled to		
	an e	electrode by which o	of the	following materials?		
				(CO3, K6)		
	(a)	Polyacrylamide	(b)	Urease		
	(c)	Ferrocene	(d)	Biochips		
7.	А	non-ionic surfac	tant	based multilamellar or		
	unilamellar vesicular structure is (CO4, K4)					
	(a)	Liposome	(b)	Niosome		
	(c)	Microspheres	(d)	Nanoparticle		

 $\mathbf{2}$

8.	Alzet is an example of ———— type of parenteral							
	syste	em.			(CO4, K4)			
	(a) Osmotic pressure activated							
	(b)	Vapour pressure a	ctiva	ted				
	(c)	Magnetically activ	rated					
	(d)	Hydration activate	ed					
9.	Nan	omaterials with ant	cioxid	ant properties ar	re (CO5, K5)			
	(a)	Nanowires	(b)	Nanotubes				
	(c)	Fullerences	(d)	Buckyballs				
10.	Nan	oshells are used in t	the tr	reatment of	(CO5, K5)			
	(a)	Cancer						
	(b)	Parkinson's diseas	se					
	(c)	Alzheimer's diseas	se					
	(d)	HIV						
		Par	rt B		$(5 \times 5 = 25)$			
A	Answer all the questions not more than 500 words each.							

Answer an the questions not more than 500 words each.

11. (a) Explain the role of carbon nanotubes in combating infectious disease. (CO1, K2)

Or

(b) Outline the biological significance of organic-inorganic hybrid nanomaterials. (CO1, K2)

3

12. (a) Discuss the role of nanopesticides in the control of pest and insect. (CO2, K6)

Or

- (b) Explain the various methods adapted application of nano-fertilizers on agricultural field. (CO2, K6)
- 13. (a) Give a brief account on biosensors for the detection of microbes in agro products. (CO3, K6)

Or

- (b) Elaborate the role of carbon based nanomaterial in bioimaging. (CO3, K6)
- 14. (a) Explain the various routes of administration of nanocarriers and mode of cellular entry. (CO4, K4)

Or

- (b) Enumerate the characteristic features of lipid based nanocarrier for drug delivery. (CO4, K4)
- 15. (a) Explain the construction and working principle of respirocytes. (CO5, K5)

Or

(b) Explain in detail the application of nanomaterial in orthopedic medicine. (CO5, K5)

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Part C $(5 \times 8 = 40)$

Answer all the questions not more than 1000 words each.

16. (a) Describe in detail about natural polymer based nanomaterial and its biomedical application.

(CO1, K2)

Or

- (b) Summarize the rote of various metal and metal oxide based nanoparticles in the field of biomedicine. (CO1, K2)
- 17. (a) Elaborate in detail the various commercially available nanofertilizer in the market and its merits over conventional fertilizer. (CO2, K6)

 \mathbf{Or}

- (b) Discuss in detail the mechanism behind enhanced nutritional intake, nitrogen fixation and photosynthesis of plants using nano—fertilizers. (CO2, K6)
- 18. (a) Elaborate in detail the surface chemistry of quantum dots and its functionalization for cell targeting and imaging. (CO3, K6)

 \mathbf{Or}

 (b) Discuss in detail the working principle of protein based sensor and its potential role in disease diagnosis. (CO3, K6)

 $\mathbf{5}$

19. (a) Classify the polymer based nanocarriers and discuss in detail its salient features as drug delivery system. (CO4, K4)

Or

- (b) Outline the steps involved in design and generation of nanobodies. Add a note on its pharmaceutical application. (CO4, K4)
- 20. (a) Elucidate the role of nanomaterial as nanotheranostic agent for targeted cancer therapy. (CO5, K5)

 \mathbf{Or}

(b) What are nanofibrous scaffold? Discuss the types of nanoscaffold and its application in tissue engineering? (CO5, K5)

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M.Sc. DEGREE EXAMINATION, NOVEMBER - 2023

Third Semester

Nanoscience and Technology

NANOELECTRONICS AND NANODEVICES

(CBCS – 2022 onwards)

Time : 3 Hours

Maximum : 75 Marks

Part A $(10 \times 1 = 10)$

Answer **all** the following objective questions by choosing the correct option.

- 1. FeRAM and DRAM happens between the ----- (CO1, K4)
 - (a) Re-written (b) Read and write
 - (c) Read only (d) Write only
- 2. In Curie -Weiss law ,the temperature is dependent of _____? (CO2, K1)
 - (a) Current
 - (b) Energy
 - (c) Dielectric constant
 - (d) Temperature
- 3. Colorimetry uses the relationship between colour intensity of a solution and the concentration of the coloured species present. Is this statement true or false? (CO1, K3)
 - (a) True (b) False

4.	The	Field Effect Transistor (FET) has (CO3, K2)							
	(a)	Very high input impedance							
	(b)	Small in Size							
	(c)	Low Power Consu	mptio	on					
	(d)	All of the above							
5.	Ball	istic spin transport	appli	cable in	(CO2, K2)				
	(a)	Nanoelectronics	(b)	Microelectronics					
	(c)	NEMS	(d)	Only (a) and (c)					
6.	Spir	ntronics developmen	nt i.e	GMR	(CO4, K2)				
	(a)	1983	(b)	1984					
	(c)	1999	(d)	1994					
7.	The	base of a transistor	is —	doped.	(CO1, K1)				
	(a)	Heavily	(b)	Moderately					
	(c)	Lightly	(d)	None of the above	9				
8.	Spir scala	ntronics materials able quantum comp	have uting	e a high promis ; as	e towards (CO2, K3)				
	(a)	Spin is almost th lived as spin inter	ne per action	rfect qubit that can is small	an be long				
	(b)	Spin can be chang	ed by	polarized light					
	(c)	Spin is a nontrivia	al qua	antum degree of fre	edom				
	(d)	All of the above							
9.	Sem elect	iconductors are - tronics.		—— on the n	nodern-day (CO2, K3)				
	(a)	Tools	(b)	Materials					
	(c)	Building block	(d)	All the above					
			2		R0270				

10.	TMI ferro	R is a component consisting of omagnets separated by a thin ————.	(CO5, K4)
	(a)	One, Insulator	
	(b)	Two, Insulator	
	(c)	One, Semiconductor	
	(d)	Two, Semiconductor	
		Part B	$(5 \times 5 = 25)$
L	Answe	er all the questions not more than 500 wor	rds each.
11.	(a)	Write brief notes on Physical Funda Nanoelectronics.	amentals of (CO1, K2)
		Or	
	(b)	Write short notes of quantum blockade e	ffect. (CO1, K2)
12.	(a)	Describe Electrochemical cells.	(CO1, K4)
		Or	
	(b)	What is Surface and Bulk Acoustic devic	ees? (CO1, K2)
13.	(a)	How sensors identify of Hazardous S Gases?	olvents and (CO1, K2)
		Or	
	(b)	Explain Calorimetric Sensors.	(CO3, K3)
14.	(a)	Write about the tools for Micro and Nar fabrication.	oelectronics (CO2, K6)
		Or	
	(b)	What is difference of FERAM and DDRA	M? (CO2, K1)

3

15.	(a)	Sketch and discuss the Quantum Well Laser.
		(CO3, K2)
		Or

(b)	Write short notes of Augment and	Virtual Reality
	(AR and VR) concept.	(CO1, K1)

Part C $(5 \times 8 = 40)$

Answer **all** the questions not more than 1000 words each.

16. (a) Give a brief note on basics of Lithographic techniques for nanoelectronics. (CO3, K4)

Or

- (b) Write in detail about Ballistic transport mechanism. (CO2, K1)
- 17. (a) What is Sensor? Explain its types and working. (CO4, K4)

Or

- (b) Describe Gas Sensitive FET. (CO5, K2)
- 18. (a) Sketch the Fe-RAM Circuit diagram and mechanism. (CO5, K6)

Or

- (b) Discuss the mechanism and working of MRAM. (CO4, K4)
- 19. (a) Sketch and explain single electron transistor (SET). (CO3, K2)

Or

- (b) What are Optical Fibers for Nanodevices? (CO1, K5)
- 20. (a) Derive Landau-Lifshitz Gilbert equation. (CO2, K1)

Or

(b) Explain Nano scale MOSFET. (CO1, K6)

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M.Sc. DEGREE EXAMINATION, NOVEMBER - 2023

Third Semester

Nanoscience and Technology

NANO ENGINEERING

(CBCS – 2022 onwards)

Time : 3 Hours

Maximum : 75 Marks

Part A $(10 \times 1 = 10)$

Answer **all** the following objective questions,

by choosing the correct option

1. What is responsible for Conduction in Semiconductor?

(CO1, K2)

- (a) Electrons only
- (b) Holes only
- (c) Both electrons and holes
- (d) neither electrons nor holes
- 2. Which of the following principle used in Holography?

(CO1, K2)

- (a) Interference (b) Diffraction
- (c) Interferometer (d) Polarization

	2 R0271							
(d)	It's a property of Hall effect sensors.							
(c)	It's the ability of a sensor to emit radiation.							
(b)	Its a phenomenon where materials generate a voltage when subjected to a temperature gradient.							
(a)	Its a measure of thermal conductivity.							
In effe	In the context of thermal sensors, what is the Seebeck effect? (CO3, K2)							
(d)	Greater resistance to environmental factor							
(c)	Enhanced sensitivity and precision							
(b)	Improved resistance to wear and tear							
(a)	Increased structural stability							
Wh sys	What is the significance of scaling down mechanical systems to the micro and nanoscale? (CO3, K2)							
(d)	Carbon-disulphide							
(c)	Carbon monosulphide							
(b)	Carbon dioxide							
(a)	Carbon-monoxide							
Wh con	at form will form graphite readily in oxyger taining atmospheres? (CO2, K3							
(c)	Boat (d) Achiral							
(a)	Armchair (b) Chiral							
nar	notubes? (CO2, K3)							

- 7. What is a 'spin-up' state for an electron in Spintronics? (CO4, K2)
 - (a) The electron is not moving
 - (b) The electron's spin is aligned in the same direction as an external magnetic field
 - (c) The electron's spin is aligned opposite to an external magnetic field.
 - (d) The electron has gained energy
- 8. What is the term for the magnetic effect resulting from the interaction between an electron's spin and its orbital motion? (CO4, K2)
 - (a) Spin alignment
 - (b) Spin relaxation
 - (c) Spin-orbit coupling
 - (d) Spin polarization
- 9. Which of the following statement is true regarding hybrid orbitals? (CO5, K1)
 - (a) The amount of orbitals formed after the hybridization is not equal to the number of orbitals before hybridization
 - (b) The hybrid orbitals don't have equal energy
 - (c) They can form more stable bonds than the pure orbitals
 - (d) Hybridization doesn't indicate geometry
- 10. Which of the following is not an application of conducting polymers? (CO5, K1)
 - (a) Rechargeable batteries
 - (b) Analytical sensors
 - (c) Electronics
 - (d) Adhesives

3

Part B $(5 \times 5 = 25)$

Answer all questions, not more than 500 words each

11. (a) Write working principle of Lorentz microscopy with schematic diagram. (CO1, K2)

Or

- (b) Explain working principle and mechanism of Electron Holography. (CO1, K2)
- 12. (a) Illustrate the properties of the carbon nanotubes. (CO2, K3)

 \mathbf{Or}

- (b) Discuss about CNTs used in Field emission and shielding applications. (CO2, K3)
- 13. (a) Explain Micro electrochemical system technology. (CO3, K2)

Or

- (b) Write the Schematic diagram and working principle of micro actuators. (CO3, K2)
- 14. (a) Briefly explain Rashba effect in spin field effect transistor. (CO4, K2)

 \mathbf{Or}

(b) Mention the concept of Datta–Das transistor.

(CO4, K2)

4

15.	(a)	What	is	liquid	crystallinity?	Explain	their
		prepar	atior	(CC	93, K1)		

Or

(b) Describe H and J aggregates. (CO3, K1)

Part C $(5 \times 8 = 40)$

Answer all the questions not more than 1000 words each

16. (a) Give a Brief note on Magnetic Force Microscopy. (CO1, K2)

Or

- (b) What is Magnetic Media and explain their properties. (CO1, K2)
- 17. (a) What is Field Effect Transistor? How to use CNT in FET applications? (CO2, K3)

Or

- (b) Discuss in detail about types of CNTs and their merits and demerits. (CO2, K3)
- 18. (a) Explain the fabrication process of Nano electronics devices. (CO3, K2)

Or

(b) Bring out significance of thermal sensor and mechanical sensor in nano electronic device.

(CO3, K2)

19. (a) Why Spintronics is important? Explain their properties. (CO4, K2)

Or

(b) Briefly explain spin relaxation in magnetic multi layers. (CO4, K2)

5	R0271

20. (a) Make a detailed note on electroluminescence from an electrochemical cell. (CO5, K1)

Or

(b) Explain about

(CO5, K1)

- (i) Hybridisation
- (ii) conjugation and
- (iii) excitations.

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M.Sc. DEGREE EXAMINATION, NOVEMBER - 2023

Third Semester

Nano Science and Technology

MICROSYSTEM TECHNOLOGY

(CBCS – 2022 onwards)

Time : 3 Hours

Maximum : 75 Marks

Part A $(10 \times 1 = 10)$

Answer **all** questions.

- 1. Thickness of thin film in the range of -----. (CO1, K1)
 - (a) Nm
 - (b) Micro meter
 - (c) Several nm to several mm
 - (d) Several nm to several micro meter

2. _____ parameter effect on Thin film formation in Thermal evaporation. (CO1, K1)

- (a) Temperature (b) Concentration
- (c) PH (d) Density

3. One of the applications of Bulk micromachining is (CO1, K1)

- (a) SAW sensor
- (b) Resonant sensor
- (c) Temperature sensor
- (d) Pressure sensor

4.		is the most used in silicon
	mici	comachining. (COI, KI)
	(a)	Laser micromachining
	(b)	Micro Electro-Discharge machining
	(c)	Bulk machining
	(d)	Powder Blasting
5.	One is	of the most used kinds of lasers in microfabrication (CO1, K1)
	(a)	Excimer
	(b)	Diamond milling
	(c)	Bulk micromachining
	(d)	None of the above
6.	Whi	ch of these is a material removal method? (CO1, K1)
	(a)	Laser Micromachining
	(b)	Laser Microelectronic
	(c)	Laser Electro-Discharge
	(d)	None of the above
7.		process is also called spark erosion. (CO1, K1)
	(a)	Ultrasonic machining
	(b)	Powder blasting
	(c)	Soft lithography
	(d)	Micro electro discharge machining
8.		
	actio	on. (CO1, K1)
	(a)	Diamond milling
	(b)	Soft lithography
	(c)	Micro-electro discharge machining
	(d)	Powder blasting

 $\mathbf{2}$

0.	(a)	Diamond milling (b) LCD milling
	(c)	Both (a) and (b) (d) None of the above
10.	Part	cicle speed of powder blasting is in the range of (CO1, K1)
	(a)	80 - 200 ms (b) $80 - 400 ns$
	(c)	80 - 200 ns (d) $80 - 200 s$
		Part B $(5 \times 5 = 25)$
	Ans	wer all questions not more than 500 words each.
11.	(a)	Brief the scope and development of the Electronic Design Automation EDA. (CO2, K3)
		Or
	(b)	Manipulate the rapid proto typing and micro ECM. (CO3, K3)
12.	(a)	Explain the difference between MEMS and microsystems. (CO2, K3)
	(b)	Microelectronics and Microelectronics (CO2, K5)
13.	(a)	Interpret the UV imaging technology. (CO2, K4) Or
	(b)	Illustrate the process of LISC. (CO3, K5)
14.	(a)	Demonstrate the MEMS performance and evaluation. (CO4, K6)
		Or
	(b)	Discuss about atomic fusion bonding. (CO3, K5)
15.	(a)	Explain the Non-silicon MEMS fabrication. (CO3, K4)
		Or
	(b)	Describe about System-on-chip (SOC). (CO4, K4)
		3 R0272

Part C $(5 \times 8 = 40)$

Answer all questions not more than 1000 words each.

16. (a) Describe physical vapor deposition with relevant diagrams. (CO4, K4)

Or

- (b) Categorize the classification of physical vapor deposition. (CO4, K4)
- 17. (a) Organize the micromachining for metals. (CO5, K4)

Or

- (b) Describe various Sealing Techniques MEMS Mechanical Sensor Packaging. (CO4, K5)
- 18. (a) Explain the process of nanoimprint lithography. (CO5, K4)

Or

- (b) Discuss the e-beam lithography technology. (CO4, K5)
- 19. (a) Examine the operation of biosensors for the detection of biological threats. (CO4, K4)

Or

- (b) Explain the operation of the pressure sensor and its packaging. (CO4, K2)
- 20. (a) Develop the biomedical MEMS. (CO5, K3)

Or

(b) Predict the integration and exploitation of microsystem. (CO4, K3)

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